	Туре	L#	Hits	Search Text	DBs	Time Stamp	Com ments	Error Definition	Errors
1	IS&R	L1	2	("20040110377").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/05 18:30			
2	BRS	L2	103300	(semiconductor or substrate) same stress\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/05 18:31			. ,
3	BRS	L3	67269	(semiconductor or substrate) with stress\$2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/05 18:31	•		
4	BRS	L4	13197	(semiconductor or substrate) same (stress\$2 with prevent\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/05 18:31			
5	BRS	L5	9092	(semiconductor or substrate) with (stress\$2 with prevent\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/05 18:32			
6	BRS	L6	500	etch\$3 same ((semiconductor or	10000. t,	2007/03/05 19:18			
7	BRS	L7	328	i e	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/05 19:30			
8	BRS	L8	578	(etch\$3 same ((transistor or FET or gate) same (sidewall))) same (conformal with oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	2007/03/05 19:30			

3/5/07, EAST Version: 2.1.0.14

	Туре	L#	Hits	Search Text	DBs	Time Stamp	Com ments	Error Definition	Errors
9	BRS	L9	396	8 and @pd<="20031114"	1	2007/03/05 19:32			
10	BRS	L10	269	(etch\$3 same ((transistor or FET or gate) same (sidewall) same (source same drain))) same (conformal with oxide)	1	2007/03/05 20:34			
11	BRS	L11	201	10 and @pd<="20031114"		2007/03/05 20:40		·	
12	BRS	L12	139	(gate or electrode)) same	USPAT; USOCR;	2007/03/05 20:36		٠	·
13	BRS	L13	106			2007/03/05 20:40			